CORRECTION

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Correction: Gate-tunable interfacial properties of in-plane ML MX$_2$ 1T′–2H heterojunctions

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Correction for 'Gate-tunable interfacial properties of in-plane ML MX$_2$ 1T′–2H heterojunctions' by Shiqi Liu *et al.*, *J. Mater. Chem. C*, 2018, DOI: 10.1039/c8tc01106k.

The authors regret that an incorrect description was used in the computational details section. The sentence ''A periodic type, a Neumann type and a Dirichlet type boundary condition are used in the x, y and z directions of the device (Fig. 4), respectively.'' should read ''A Neumann type, a Periodic type and a Dirichlet type boundary condition are used in the x, y and z directions of the device (Fig. 4), respectively.''

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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